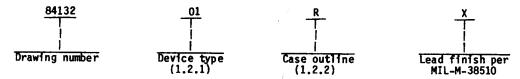
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		EN	r c	A(	GE	c	OE	ÞΕ	67	26	8					<b>I</b>										
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### 1. SCOPE

- $1.1\,$  Scope. This drawing describes device requirements for class B microcircuits in accordance with  $1.2.1\,$  of MIL-STD-883, "Provisions for the use of MIL-STD-883 in conjunction with compliant non-JAN devices".
  - 1.2 Part number. The complete part number shall be as shown in the following example:



1.2.1 Device types. The device types shall identify the circuit function as follows:

Device type	Generic number	Circuit function	Access time
01			85 ns
02			45 ns
03	(see 6.4)	(16K x 1 SRAM)	70 ns
04		<b>,</b>	35 ns
05			35 ns
06			25 ns
07			25 ns
08			55 ns
09			45 ns

1.2.2 <u>Case outlines</u>. The case outlines shall be as designated in appendix C of MIL-M-38510, and as follows:

# <u>Outline letter</u>

### Case outline

R	D-8 (20-lead, 1.060" x .310" x .200"), dual-in-line package
S	F-9 (20-lead, .540" x .300" x .100"),flat package
Υ	C-13 (20-terminal, .440" x .305" x .120"), leadless chip carrier
	package

1.3 Absolute maximum ratings.

Supply voltage range (V <sub>CC</sub> ) Storage temperature range	-0.3 V dc to +7.0 V dc 1/
Maximum power dissipation (P <sub>D</sub> ) Lead temperature (soldering, 5 seconds) Thermal resistance (A <sub>10</sub> )	1.0 W +270°C See MIL-M-38510, appendix C
Thermal resistance $(\theta_{JC})$ Junction temperature $(T_J)$ 2/	+150°C

1.4 Recommended operating conditions.

Case operating	temperature	range		 -	_	 	-	-55°C to +125°C	
Supply voltage	range (V <sub>CC</sub> )		-	 -	-	 	-	4.5 V dc to 5.5 V dc 1	1/

- 1/ All voltages referenced to  $V_{SS}$ .
- $\frac{2}{100}$  Maximum junction temperature shall not be exceeded except for allowable short duration burn-in screening conditions as specified in method 5004 of MIL-STD-883.

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### 2. APPLICABLE DOCUMENTS

2.1 Government specification and standard. Unless otherwise specified, the following specification and standard, of the issue listed in that issue of the Department of Defense Index of Specifications and Standards specified in the solicitation, form a part of this specification to the extent specified herein.

**SPECIFICATION** 

MILITARY

MIL-M-38510

Microcircuits, General Specification for.

STANDARD

MILITARY

MIL-STD-883

Test Methods and Procedures for Microelectronics.

(Copies of specification and standard required by manufacturers in connection with specific acquisition functions should be obtained from the contracting activity or as directed by the contracting activity.)

- 2.2 Order of precedence. In the event of a conflict between the text of this drawing and the references cited herein, the text of this drawing shall take precedence.
  - REQUIREMENTS
- 3.1 Item requirements. The individual item requirements shall be in accordance with 1.2.1 of MIL-STD-883, "Provisions for the use of MIL-STD-883 in conjunction with compliant non-JAN devices" as specified herein.
- 3.2 Design, construction, and physical dimensions. The design, construction, and physical dimensions shall be as specified in MIL-M-38510 and herein.
  - 3.2.1 <u>Terminal connections</u>. The terminal connections shall be as specified on figure 1.
  - 3.2.2 Truth table. The truth table shall be as specified on figure 2.
  - 3.2.3 Block diagram. The block diagram shall be as specified on figure 3.
  - 3.2.4 <u>Case outlines</u>. The case outlines shall be in accordance with 1.2.2 herein.
- 3.2.5 Die overcoat. Polyimide and silicone coatings are allowable as an overcoat on the die for alpha particle protection provided that each coated microcircuit inspection lot as specified in MIL-M-38510, shall be subjected to and pass the internal moisture content test, (method 1018 of MIL-STD-883), the frequency of the internal water vapor testing may not be decreased unless approved by the preparing activity.
- 3.3 <u>Electrical performance characteristics</u>. Unless otherwise specified, the electrical performance characteristics are as specified in table I and apply over the full case operating temperature range.
- 3.4 Marking. Marking shall be in accordance with MIL-STD-883 (see 3.1 herein). The part shall be marked with the part number listed in 1.2 herein. In addition, the manufacturer's part number may also be marked as listed in 6.4 herein.

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		TABLE I. Elec	trical per	rforman	ce characte	ristics.				
Test	Symbol	-55° (	onditions C < T <sub>C</sub> < 1 4.5 V < otherwise	125°C	5.5 V 1ed	Group A  subgroups	  Device   type	Lim	its   Max	Unit
Supply current (operating)	I <sub>CC1</sub>	Address cycling ICE = V <sub>IL</sub> , I <sub>O</sub> =	), f= 1/t <sub>A</sub> 0 A	lVAV (m	inimum)	1,2,3	01,03 02,05, 07,08, 09	 	50       100   70	l mA
Supply current TTL standby	I <sub>CC2</sub>	Address stable CE = WE = V <sub>IH</sub>	, I <sub>O</sub> = 0 A			1,2,3	01,03 02,08 04,05, 06		15 15 20 25 25	mA
Supply current CMOS standby	I <sub>CC3</sub>	$\begin{vmatrix} CE = V_{CC} - 0.2 \\ V_{IN} \ge V_{CC} - 0.2 \end{vmatrix}$	V, I <sub>0</sub> = 0 V OR < 0	.2 V			01,03 04,06 07		100 900 10	μΑ
Supply current (data retention)	Icc4	V <sub>CC</sub> = 2.0 V,I <sub>0</sub> CE = WE = V <sub>CC</sub>	= 0 A			Į.	01,03 09,04, 06		40 200	μΑ
Low level output voltage	VOL	V <sub>CC</sub> = 4.5 V; I <sub>O</sub>	L = 8 mA			1,2,3	A11		0.4	V
High level output voltage	v <sub>он</sub>	$V_{CC} = 4.5 \text{ V}; I_0$	H = -4 mA			1,2,3	A11	2.4		٧
Input leakage current	IIIH	V <sub>IN</sub> = GND   V <sub>IN</sub> = 5.5 V 				1,2,3     	01,03 02,05 07,09 04,06 08	-1.0 -10 -5	1.0 10	μА
High impedance output leakage	IOHZ	V <sub>OUT</sub> = 5.5 V	CE = V(	cc			01,03	-1.0	1.0	
current	IOLZ	V <sub>OUT</sub> = GND	ICE = V1	CH .		1,2,3	07 02,05 08,09 04,06	-10 -20	10 20 5	μА
Low level input voltage	VIL					1,2,3	All		0.8	٧
High level input voltage	VIH					1,2,3	I I I	2.2	-   	٧
Input capacitance		  T <sub>C</sub> = +25°C, V <sub>CC</sub>  V <sub>IN</sub> = GND, f = 1  See 4.3.1c	= GND MHz			4	All		8	pF
Output capacitance		T <sub>C</sub> = +25°C, V <sub>CC</sub>  V <sub>OUT</sub> = GND, f =  See 4.3.1c	= GND 1 MHz			4	A11		10	pF
See footnotes at				1		·				
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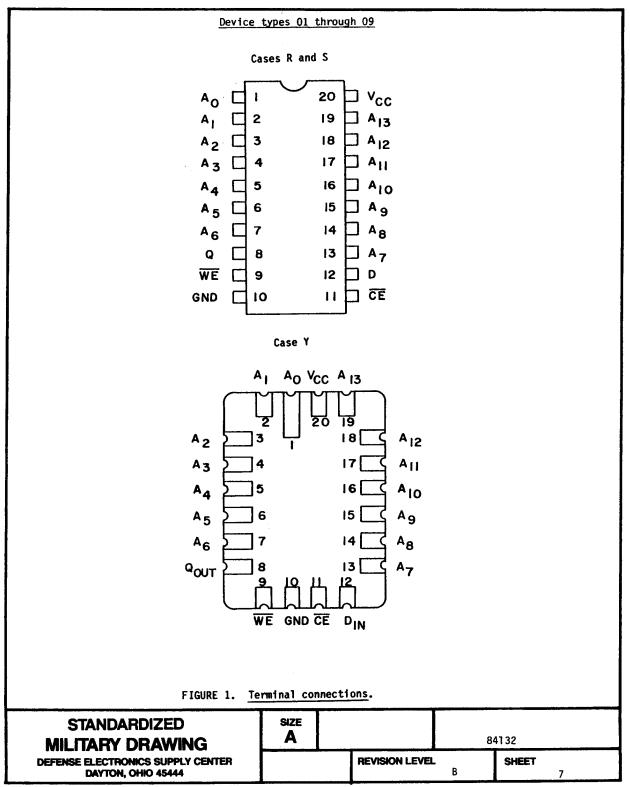
	TABLE	I. Electrical	performan	ce char	racteristic	<u>s</u> - Contin	ued.			
Test	Symbol	-55°0   V <sub>SS</sub> = 0 V	onditions C < T <sub>C</sub> < + 4.5 V < v otherwise :	1 <b>2</b> 5°C Vcc < 5	 5.5 V	  Group A  subgroups 	  Device   type 		its     Max 	  Unit 
Read or write cycle time	t <sub>AVAV</sub>	See	e figure 5			9,10,11	01 02,09 03 08 04,05 06,07	85 45 70 55 35 25		ns
Address access time	t <sub>AVQV</sub>				_	9,10,11	01 02,09 03 08 04,05 06,07		85 45 70 55 35 25	İ
Chip enable access time	t <sub>ELQV</sub>				 	9,10,11	01 02,09 03 08 04,05 06,07		85 45 70 55 35 25	ĺ
Chip enable to output in high Z	teHQZ 2/						01,03   02,08,   05,09   04   06,07		40 25 15 10	   
Output hold after address change	tavox 2/				     	 	01,03, 04,06, 07   02,05, 08,09	3 ]		l ns
Chip enable to output active	t <sub>ELQX</sub>				 	<u>[</u>	01,03, 07 02,08,	5 3		ns
Write enable pulse width during write	twLwH				       	] [	01   03,08   02,04,  05,09	45   40   30   20		ns
Chip enable to end of write ee footnotes at	telwh	ble.			       	#   [] 	01   02,09   03   04,05   08   06,07	65   35   55   30   45   20		ns
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				γ	Limi	ts	T
Test	Symbol	Conditions 1/3/4/ -55°C < T <sub>C</sub> < +125°C V <sub>SS</sub> = 0 V 4.5 V < V <sub>CC</sub> < 5.5 V unless otherwise specified	Group A  subgroups 	Device   type 	Min	Max	Unii   
Data setup to end of write	t <sub>DVWH</sub>	See figure 5	9,10,11	01   02,08,   09   03   04,05   06,07	35 25 30 25 15		ns
Data hold after end of write	t <sub>WHDX</sub>		9,10,11	A11	5	· · · · · · · · · · · · · · · · · · ·	ns
Address setup to end of write	t <sub>AVWH</sub>		9,10,11	01 02,09 03 04,05 06,07	65   35   55   30   20   45		ns
Write recovery time	t <sub>WHAV</sub>				5		ns
Write-enable low to output in high Z	twLQZ 2/			01,03   02,09   08   05   04   06,07		40 30 25 20 15	ns
Write-enable high to output i invalid	twhox 2/		9,10,11	ATT	0		ns
Address setup   before write   low	<sup>t</sup> AVWL			01,03, 04,06, 07	0		ns

- $\underline{1}$ / All voltages referenced to  $V_{SS}$ .
- $\underline{2}/$  Tested initially and after any design and or process changes which may affect this parameter.
- $\frac{3}{}$  AC measurements assume transition time < 5 ns and input level are from VSS to 3.0 V. See figure 5. Timing transitions are at 1.5 V.
- 4/ For timing waveforms, see figure 4.

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Device types 01 through 09

Mode	CE	WE	Output	Power
Standby	Н	Х	High Z	Standby
Read	L	Н	D <sub>OUT</sub>	Active
Write	L	L	High Z	Active

FIGURE 2. Truth table.

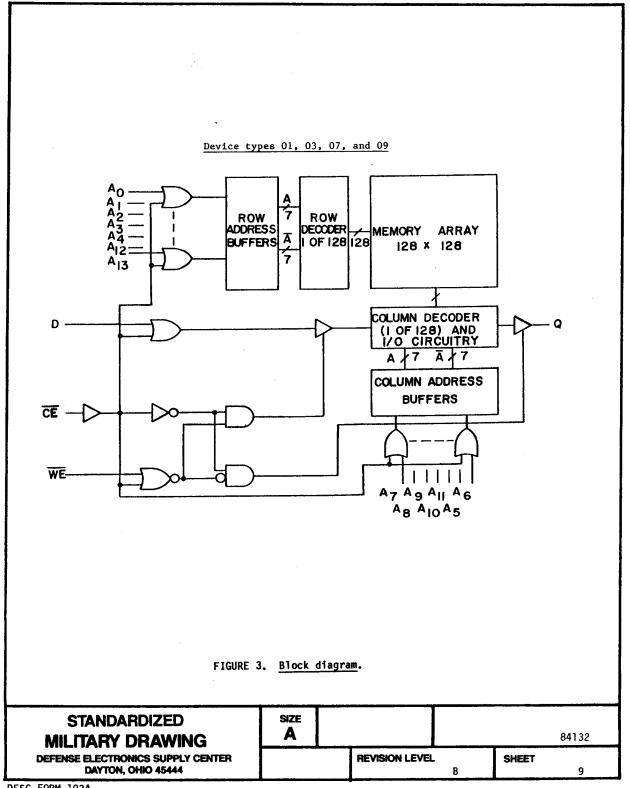
STANDARDIZED
MILITARY DRAWING
DEFENSE ELECTRONICS SUPPLY CENTER
DAYTON, OHO 45444

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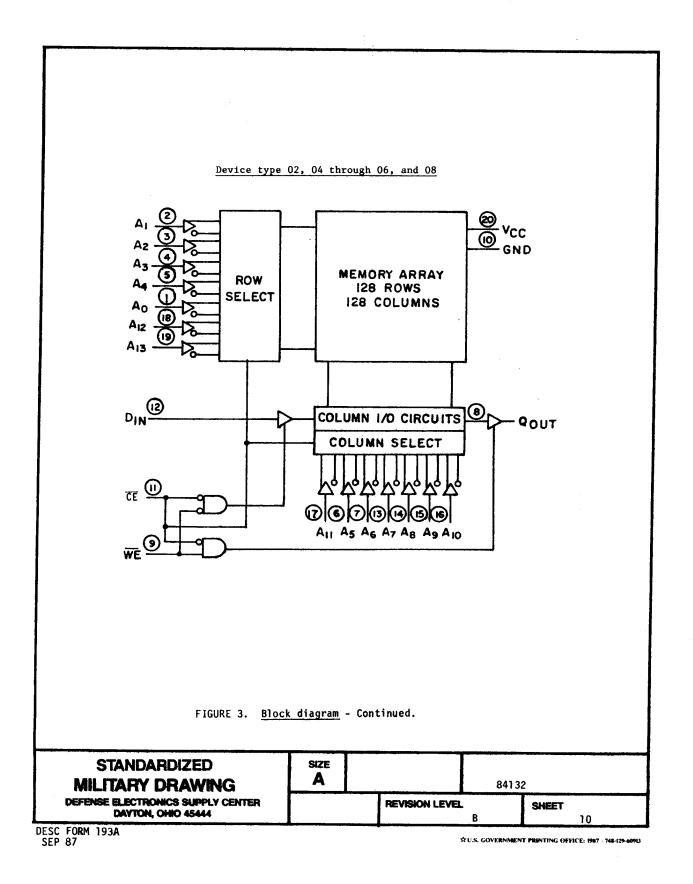
DESC FORM 193A SEP 87

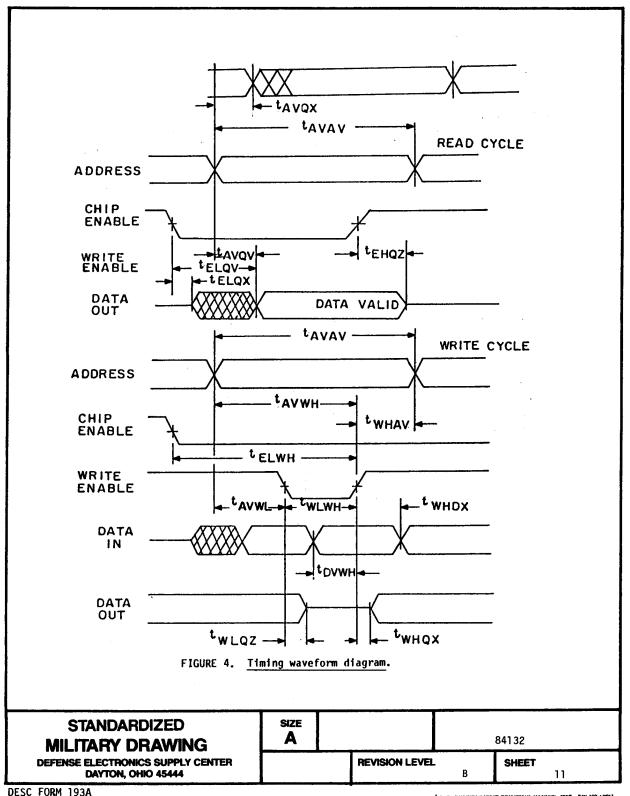
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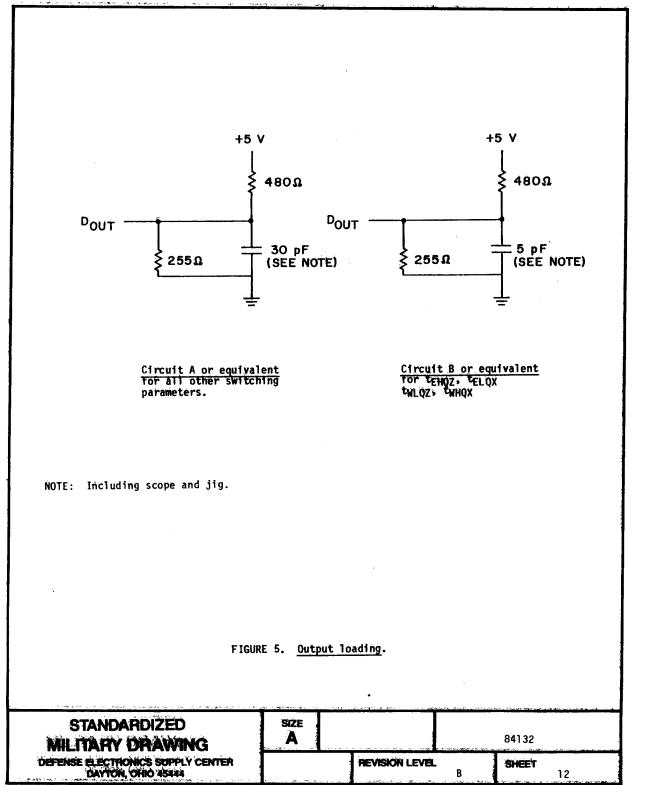
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- 3.5 <u>Certificate of compliance</u>. A certificate of compliance shall be required from a manufacturer in order to be listed as an approved source of supply in 6.4. The certificate of compliance submitted to DESC-ECS prior to listing as an approved source of supply shall state that the manufacturer's product meets the requirements of MIL-STD-883 (see 3.1 herein) and the requirements herein.
- 3.6 Certificate of conformance. A certificate of conformance as required in MIL-STD-883 (see 3.1 herein) shall be provided with each lot of microcircuits delivered to this drawing.
- 3.7 Notification of change. Notification of change to DESC-ECS shall be required in accordance with MIL-STD-883 (see 3.1 herein).
- 3.8 <u>Verification and review</u>. DESC, DESC's agent, and the acquiring activity retain the option to review the manufacturer's facility and applicable required documentation. Offshore documentation shall be made available onshore at the option of the reviewer.
  - 4. QUALITY ASSURANCE PROVISIONS
- 4.1 Sampling and inspection. Sampling and inspection procedures shall be in accordance with section 4 of MIL-M-38510 to the extent specified in MIL-STD-883 (see 3.1 herein).
- 4.2 <u>Screening.</u> Screening shall be in accordance with method 5004 of MIL-STD-883, and shall be conducted on all devices prior to quality conformance inspection. The following additional criteria shall apply:
  - a. Burn-in test, method 1015 of MIL-STD-883.
    - Test condition A, B, C, or D using the circuit submitted with the certificate of compliance (see 3.5 herein).
    - (2)  $T_A = +125$ °C, minimum.
  - b. Interim and final electrical test parameters shall be as specified in table II herein, except interim electrical parameter tests prior to burn-in are optional at the discretion of the manufacturer.
- 4.3 Quality conformance inspection. Quality conformance inspection shall be in accordance with method 5005 of MIL-STD-883 including groups A, B, C, and D inspections. The following additional criteria shall apply.
  - 4.3.1 Group A inspection.
    - a. Tests shall be as specified in table II herein.
    - b. Subgroups 5 and 6 in table I, method 5005 of MIL-STD-883 shall be omitted.
    - c. Subgroup 4 (C  $_{\hbox{IN}}$  and C  $_{\hbox{OUT}}$  measurement) shall be measured only for the initial test and after process or design changes which may affect capacitance.
    - d. Subgroups 7 and 8 shall test sufficent to verify the truth table.

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### TABLE II. Electrical test requirements.

MIL-STD-883 test requirements	Subgroups   (per method   5005, table I)
Interim electrical parameters   (method 5004)	
Final electrical test parameters   (method 5004)	1*,2,3,9
Group A test requirements (method 5005)	1,2,3,4**,7***, 8***,9,10,11
Groups C and D end-point electrical parameters (method 5005)	2,8(125°C),10

PDA applies to subgroup 1.

## 4.3.2 Groups C and D inspections.

- a. End-point electrical parameters shall be as specified in table II herein.
- b. Steady-state life test conditions method 1005 of MIL-STD-883.
  - (1) Test condition A, B, C, or D using the circuit submitted with the certificate of compliance (see 3.5 herein).
  - (2)  $T_A = +125^{\circ}C$ , minimum.
  - (3) Test duration: 1,000 hours, except as permitted by method 1005 of MIL-STD-883.

### 5. PACKAGING

5.1 Packaging requirements. The requirements for packaging shall be in accordance with MIL-M-38510.

#### 6. NOTES

- 6.1 Intended use. Microcircuits conforming to this drawing are intended for use when military specifications do not exist and qualified military devices that will perform the required function are not available for OEM application. When a military specification exists and the product covered by this drawing has been qualified for listing on QPL-38510, the device specified herein will be inactivated and will not be used for new design. The QPL-38510 product shall be the preferred item for all applications.
  - 6.2 Replaceability. Replaceability is determined as follows:
    - a. Microcircuits covered by this drawing will replace the same generic device covered by a contractor-prepared specification or drawing.
    - b. When a QPL source is established, the part numbered device specified in this drawing will be replaced by the microcircuit identified as part number M38510/2910XBXX.

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<sup>\*\*</sup> See 4.3.1c.

<sup>\*\*\*</sup> See 4.3.1d.

- 6.3 Comments. Comments on this drawing should be directed to DESC-ECS, Dayton, Ohio 45444, or telephone 513-296-5375.
- 6.4 Approved sources of supply. Approved sources of supply are listed herein. Additional sources will be added as they become available. The vendors listed herein have agreed to this drawing and a certificate of compliance (see 3.5 herein) has been submitted to DESC-ECS.

Vendor     Military drawing   CAGE     part number   number		Vendor similar part number 1/	Replacement military specificatio part number			
8413201RX	34371	  HM1-65262/883	M38510/29103BRX			
8413201YX	34371	  HM4-65262/883	M38510/29103BYX			
8413202RX	<u>2</u> / 	MD51C67-45/B   CY7C167-45DMB   IMS1403S-45M   IDT6167LA45LB	M38510/29106BRX   			
8413202SX	65786 61772	  CY7C167-45KMB  IDT6167LA45FB				
8413202YX	65786 60911 61772	  CY7C167-45LMB  IMS1403N-45  IDT6167LA45LB	M38510/29106BYX			
8413203RX	34371	   HM1 -65262B/883				
8413203YX	34371	   HM4-65262B/883				
8413204RX	61772	IDT6167LA35DB				
8413204SX	61772	   IDT6167LA35FB				
8413204YX	61772	IDT6167LA35LB				
8413205RX	34649   65786   61772   60911	MD51C67-35/B   CYC7C167-35DMB   IDT6167SA35DB   IMS1403S-35M				
8413205SX	65786 61772	CY7C167-35KMB IDT6167SA35FB				
8413205YX		CY7C167-35LMB IDT6167SA35LB IMS1403N-35M				
8413206RX	61772	IDT6167SA25DB				
8413206SX	61772	IDT6167SA25FB				
8413206YX	61772	IDT6167SA25LB				

See footnotes at end of table.

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Military drawing part number			Replacement  military specification   part number
8413207RX   61772		   IDT6167LA25DB	
8413207SX	61772	1DT6167LA25FB	
8413207YX	61772	   1DT6167LA25LB	
8413208RX	   60911   34649	   IMS1403S-55M  MD51C67-55/B	
8413208YX	60911	IMS1403N-55M	
8413209RX 8413209SX	61772	   IDT6167LA45LB   IDT6167LA45LB	
8413209YX	61772	IDT6167LA45LB	1

<sup>2/</sup> Caution. Do not use this number for item acquisition. Items acquired to this number may not satisfy the performance requirements of this drawing.

drawing.
2/ Inactive for new design. Use MIL-M-38510/29106BRX.

Vendor CAGE number	Vendor name and address
34371	Harris Semiconductor P.O. Box 883 Melbourne, FL 32901
34649	Intel 5000 W. Williams Field Road Chandler, AZ 85224
60911	INMOS Corporation 1110 Bayfield Drive Colorado Springs, CO 80935-6000
61772	Integrated Device Technology Static Ram Division 1566 Moffett Street Salinas, CA 93905
65786	Cypress Semiconductor Corporation 3901 North First Street San Jose, CA 95134

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